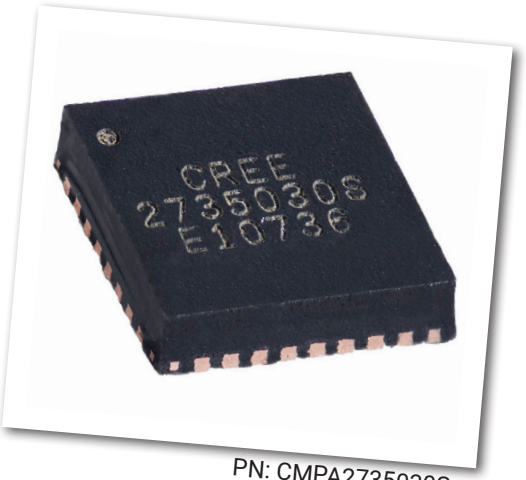
CMPA2735030S

30 W, 2.7 - 3.5 GHz, GaN MMIC, Power Amplifier

Cree's CMPA2735030S is a gallium nitride (GaN) High Electron Mobility Transistor (HEMT) based monolithic microwave integrated circuit (MMIC). GaN has superior properties compared to silicon or gallium arsenide, including higher breakdown voltage, higher saturated electron drift velocity and higher thermal conductivity. GaN HEMTs also offer greater power density and wider bandwidths compared to Si and GaAs transistors. This MMIC contains a two-stage reactively matched amplifier design approach enabling high power and power added efficiency to be achieved in a 5mm x 5mm, surface mount (QFN package).



PN: CMPA2735030S
Package: 5x5 mm

Typical Performance Over 2.7-3.5 GHz (T_c = 25°C)

Parameter	2.7 GHz	2.9 GHz	3.1 GHz	3.3 GHz	3.5 GHz	Units
Small Signal Gain	35	33	33	34	35	dB
Saturated Output Power	35	43	46	42	33	W
Power Gain	24.6	25.3	25.6	25.3	24.2	dB
PAE	61	59	57	58	57	%

Note: P_{IN} = 21 dBm, Pulse Width = 500 µs; Duty Cycle = 10%

Features

- 34 dB Small Signal Gain
- 41 W Typical P_{SAT}
- Operation up to 50 V
- High Breakdown Voltage
- High Temperature Operation
- 5 mm x 5 mm Total Product Size

Applications

- Civil and Military Pulsed Radar Amplifiers

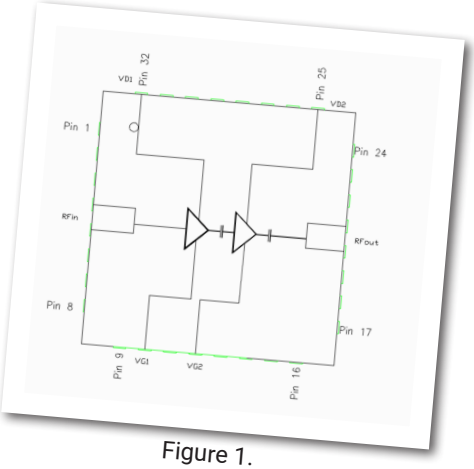


Figure 1.

Absolute Maximum Ratings (not simultaneous) at 25˚C

Parameter	Symbol	Rating	Units	Conditions
Drain-source Voltage	V_{DSS}	150	VDC	25°C
Gate-source Voltage	V_{GS}	-10, +2	VDC	25°C
Storage Temperature	T_{STG}	-65, +150	˚C	
Operating Junction Temperature	T_J	225	˚C	
Maximum Forward Gate Current	I_G	6	mA	25°C
Soldering Temperature	T_S	220	˚C	
Thermal Resistance, Junction to Case (packaged)	$R_{\theta JC}$	TBD	˚C/W	500 µsec, 10%, 85°C
Thermal Resistance, Junction to Case (packaged)	$R_{\theta JC}$	TBD	˚C/W	CW, 85°C

Electrical Characteristics (Frequency = 2.9 GHz to 3.5 GHz unless otherwise stated; T_C = 25˚C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics						
Gate Threshold Voltage	$V_{GS(TH)}$	-3.8	-3.0	-2.3	V	V_{DS} = 10 V, I_D = 6 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–	V_{DC}	V_{DD} = 50 V, I_{DQ} = 135 mA
Saturated Drain Current[1]	I_{DS}	–	6	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BD}	–	150	–	V	V_{GS} = -8 V, I_D = 6 mA
RF Characteristics[2,3]						
Small Signal Gain$_1$	S21	–	34.6	–	dB	V_{DD} = 50 V, I_{DQ} = 135 mA, Freq = 2.7 GHz
Small Signal Gain$_2$	S21	–	33.3	–	dB	V_{DD} = 50 V, I_{DQ} = 135 mA, Freq = 3.1 GHz
Small Signal Gain$_3$	S21	–	34.5	–	dB	V_{DD} = 50 V, I_{DQ} = 135 mA, Freq = 3.5 GHz
Power Output$_1$	P_{OUT}	–	34.8	–	W	V_{DD} = 50 V, I_{DQ} = 135 mA, P_{IN} = 21 dBm, Freq = 2.7 GHz
Power Output$_2$	P_{OUT}	–	46.3	–	W	V_{DD} = 50 V, I_{DQ} = 135 mA, P_{IN} = 21 dBm, Freq = 3.1 GHz
Power Output$_3$	P_{OUT}	–	33.0	–	W	V_{DD} = 50 V, I_{DQ} = 135 mA, P_{IN} = 21 dBm, Freq = 3.5 GHz
Power Added Efficiency$_1$	PAE	–	61.3	–	%	V_{DD} = 50 V, I_{DQ} = 135 mA, Freq = 2.7 GHz
Power Added Efficiency$_2$	PAE	–	58.7	–	%	V_{DD} = 50 V, I_{DQ} = 135 mA, Freq = 3.1 GHz
Power Added Efficiency$_3$	PAE	–	56.9	–	%	V_{DD} = 50 V, I_{DQ} = 135 mA, Freq = 3.5 GHz
Power Gain	G_P	–	25	–	dB	V_{DD} = 50 V, I_{DQ} = 135 mA
Input Return Loss	S11	–	-11	–	dB	V_{DD} = 50 V, I_{DQ} = 135 mA
Output Return Loss	S22	–	-8	–	dB	V_{DD} = 50 V, I_{DQ} = 135 mA
Output Mismatch Stress	VSWR	–	–	5 : 1	Ψ	No damage at all phase angles, V_{DD} = 50 V, I_{DQ} = 135 mA, P_{OUT} = 30 W Pulsed

Notes:

[1] Scaled from PCM data.

[2] All data tested in CMPA2735030S-AMP1

[3] Pulse Width = 500 µs; Duty Cycle = 10%

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Typical Performance of the CMPA2735030S

Figure 1. - Gain and Return Loss vs Frequency of the CMPA2735030S Measured in CMPA2735030S-AMP1 Amplifier Circuit
V_{DD} = 50 V, I_{DQ} = 135 mA

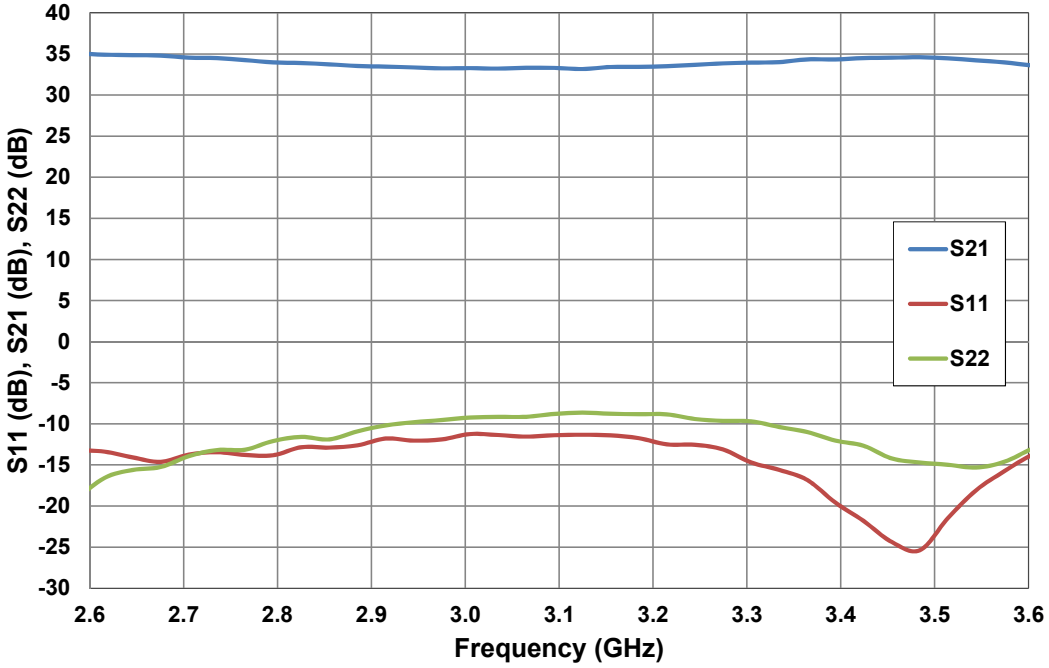

Figure 2. - Output Power, Gain and PAE vs Frequency of the CMPA2735030S Measured in CMPA2735030S-AMP1 Amplifier Circuit.
V_{DD} = 50 V, I_{DQ} = 135 mA, Pulse Width = 500 µS, Duty Cycle = 10%

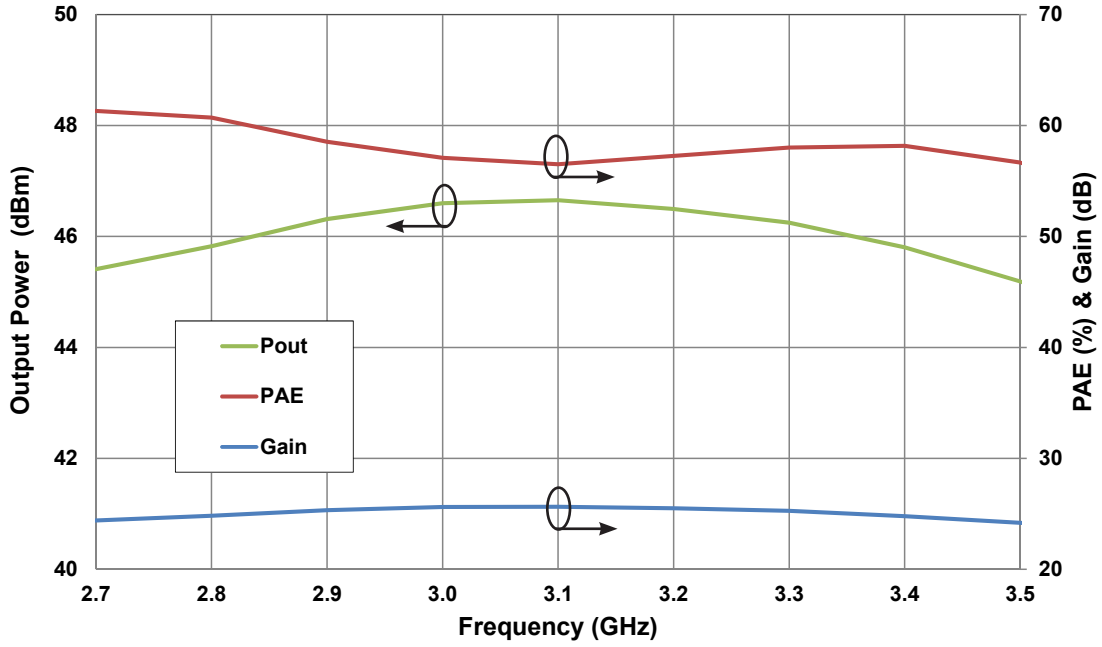

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Figure 3. - Gain and Power Added Efficiency vs Output Power
Measured in CMPA2735030S-AMP1 Amplifier Circuit
V_{DD} = 50 V, I_{DQ} = 135 mA, Frequency = 2.7 GHz

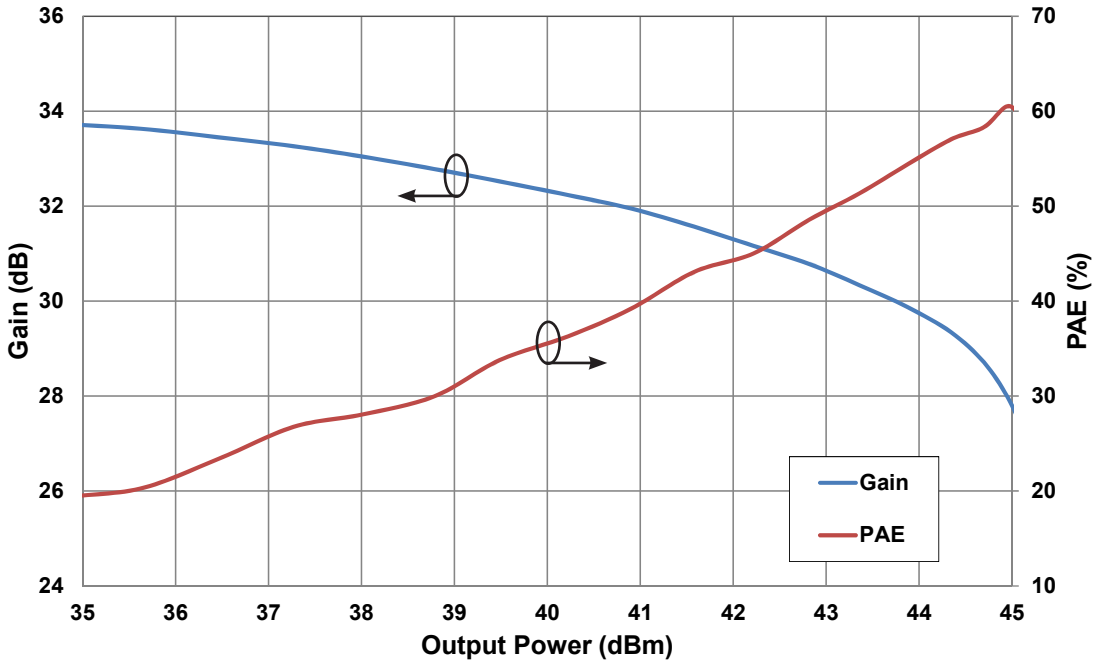
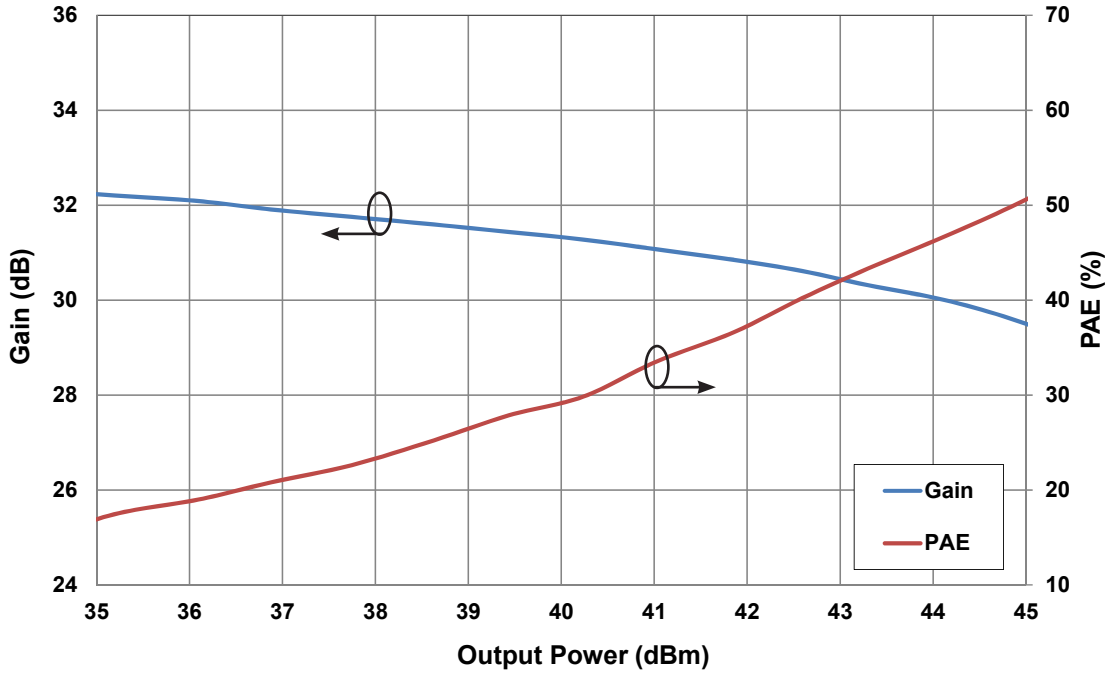


Figure 4. - Gain and Power Added Efficiency vs Output Power
Measured in CMPA2735030S-AMP1 Amplifier Circuit
V_{DD} = 50 V, I_{DQ} = 135 mA, Frequency = 3.1 GHz



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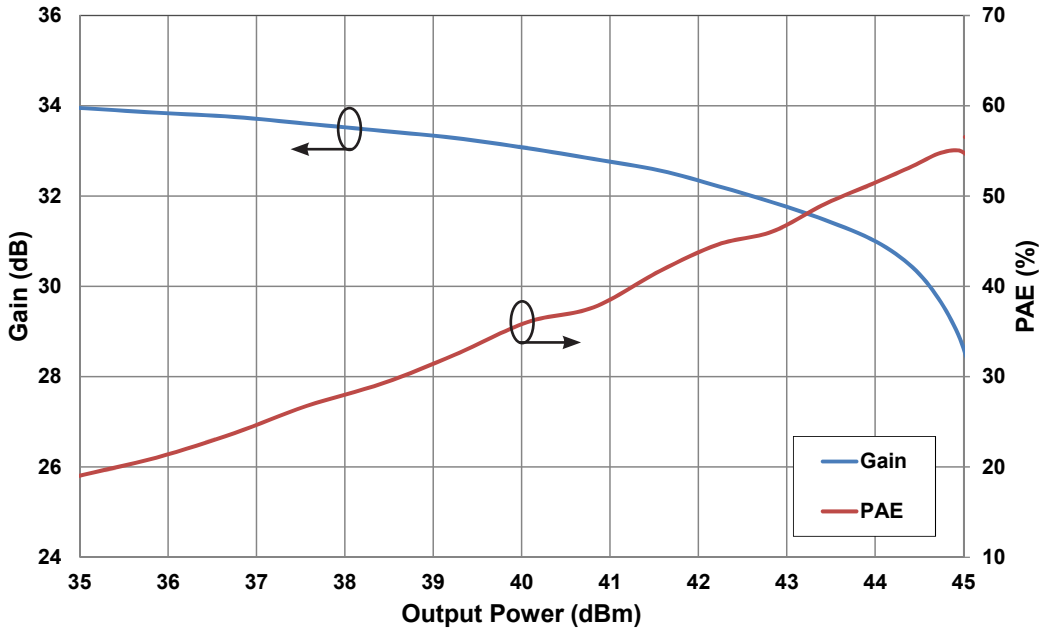
Typical Performance of the CMPA2735030S

Figure 5. - Gain and Power Added Efficiency vs Output Power
Measured in CMPA2735030S-AMP1 Amplifier Circuit
V_{DD} = 50 V, I_{DQ} = 135 mA, Frequency = 3.5 GHz



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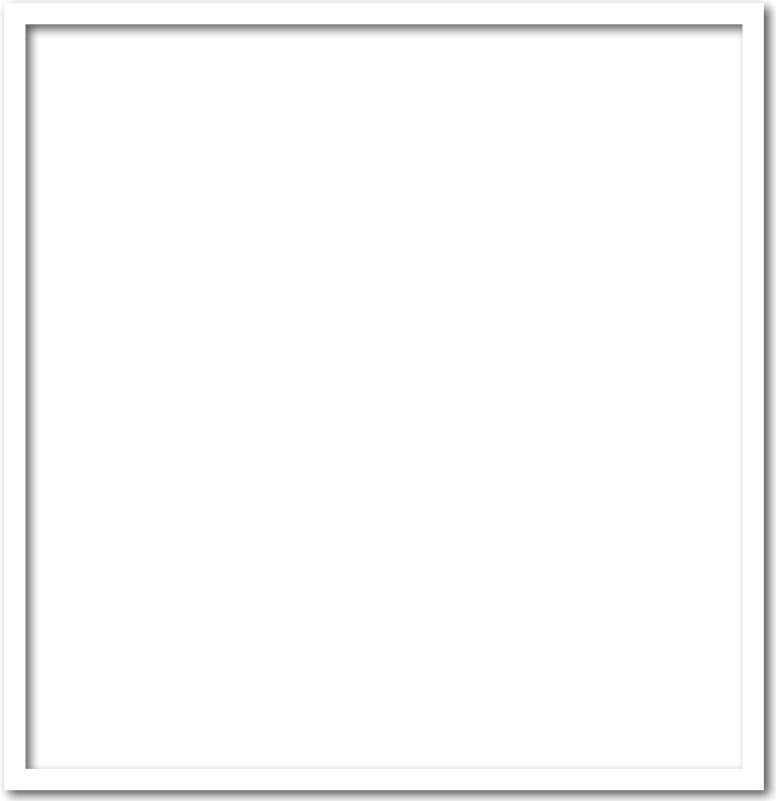
CMPA2735030S-AMP1 Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
C1, C4, C10, C11	CAP, 470pF, 100V, 0603	4
C2, C3	CAP, 100pF, 100V, 0603	2
C5, C6, C8, C9	CAP, 10pF, 100V, 0402	4
C7	CAP, 33uF, 50V, ELECT, MVY, SMD	1
C12,C13	CAP, 10uF, 16V, TANTALUM, SMD	2
R1, R2	RES, 100Ohm, 1/16W, 0603	2
J1, J2	CONNECTOR, N-TYPE, FEMALE, W/0.500 SMA FLNG	2
J3, J4	CONNECTOR, HEADER, RT>PLZ .1CEN LK 5POS	2
-	PCB, RO4350B, E_R = 3.48, h = 10 mil	1
Q1	CMPA2735030S	1

CMPA2735030S-AMP1 Demonstration Amplifier Circuit



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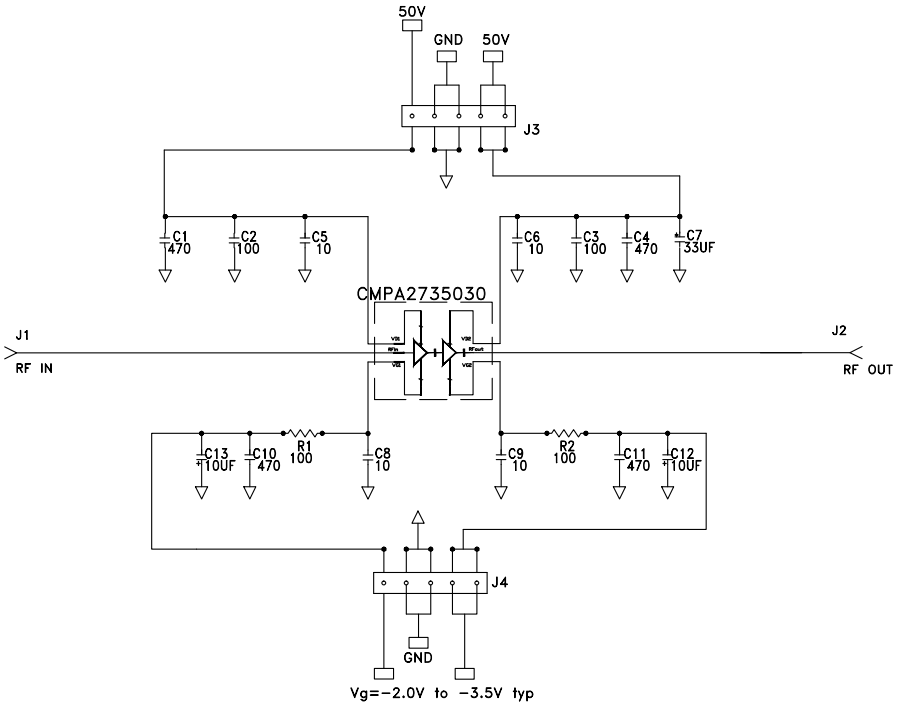
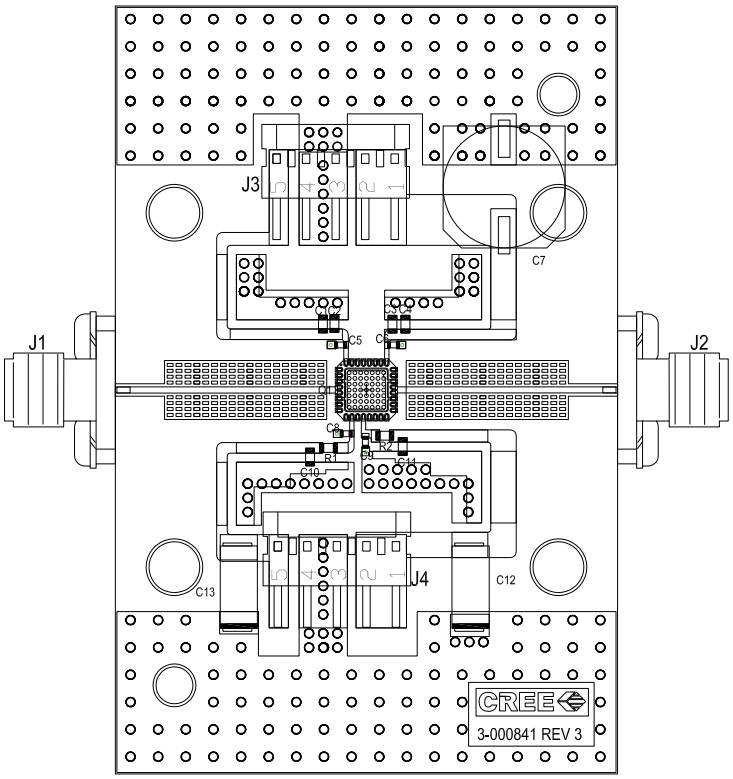
CMPA2735030S-AMP1 Demonstration Amplifier Circuit Schematic



CMPA2735030S-AMP1 Demonstration Amplifier Circuit Outline



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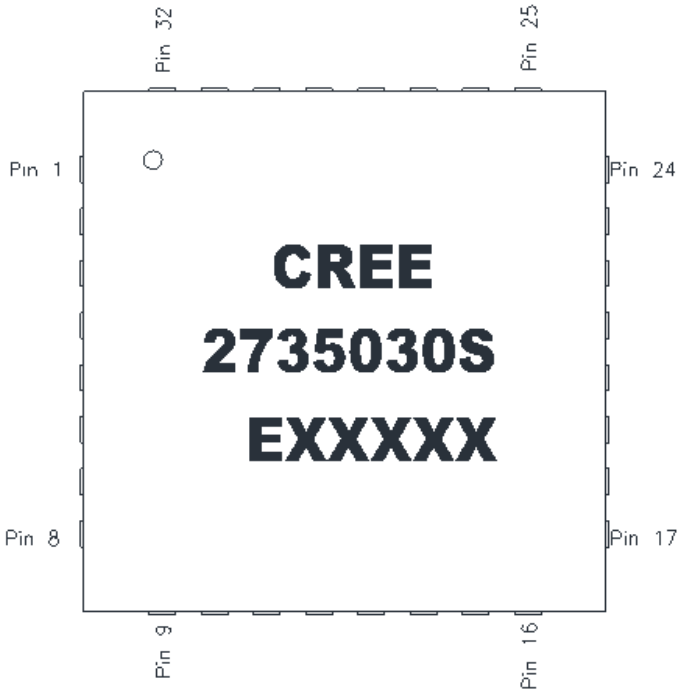
Product Dimensions CMPA2735030S (Package)

Pin	Input/Output
1,2,3	NC
4	RF IN
5	RF IN
6,7,8,9	NC
10	VG1
11	NC
12	VG2
13,14,15,16	NC
17,18,19	NC
20	RF OUT
21	RF OUT
22,23,24	NC
25	VD2
26,27,28,29	NC
30,31	NC
32	VD1



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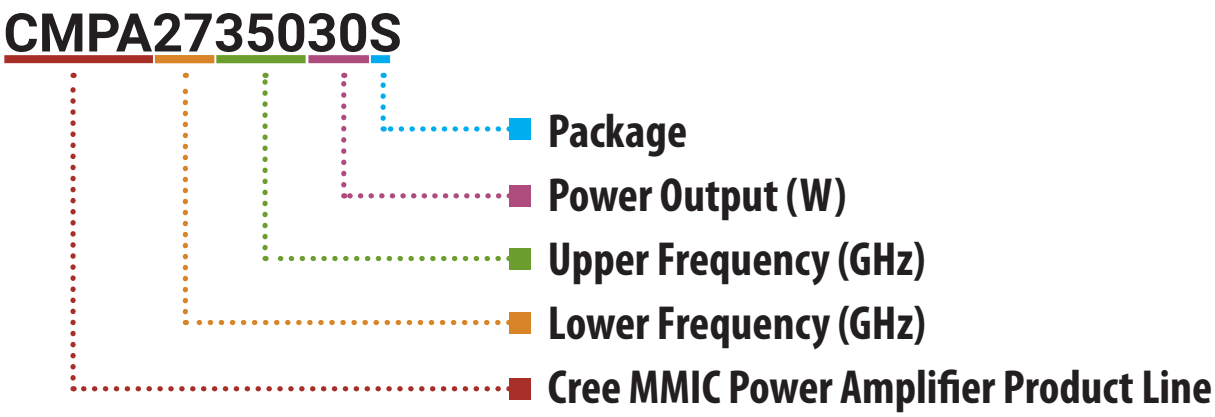
Part Number System



Parameter	Value	Units
Lower Frequency	2.7	GHz
Upper Frequency	3.5	GHz
Power Output	30	W
Package	Surface Mount	-

Table 1.

Note: Alpha characters used in frequency code indicate a value greater than 9.9 GHz. See Table 2 for value.

Character Code	Code Value
A	0
B	1
C	2
D	3
E	4
F	5
G	6
H	7
J	8
K	9
Examples:	1A = 10.0 GHz 2H = 27.0 GHz

Table 2.

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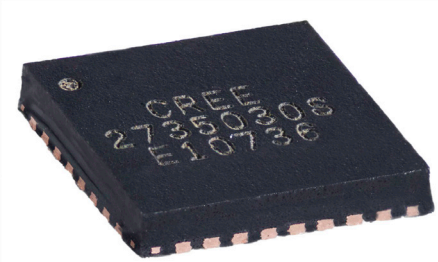
Product Ordering Information

Order Number	Description	Unit of Measure	Image
CMPA2735030S	GaN HEMT	Each	
CMPA2735030S-AMP1	Test board with GaN MMIC installed	Each	

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